

DMN3025LFV

#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	18mΩ @ V <sub>GS</sub> = 10V	25A
30V	30mΩ @ V <sub>GS</sub> = 4.5V	20A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

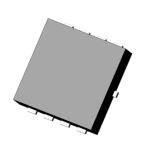
## **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

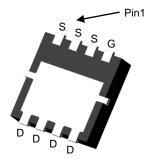
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.072 grams (Approximate)

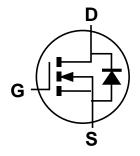
#### PowerDI3333-8 (Type UX)



Top View



**Bottom View** 



**Equivalent Circuit** 

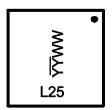
#### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN3025LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMN3025LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## Marking Information



L25= Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 17 = 2017)

WW = Week Code (01 to 53)



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 7) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		I <sub>D</sub>	25 20	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	55	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	3	Α	
Avalanche Current, L = 0.1mH (Note 8)	I <sub>AS</sub>	14	Α	
Avalanche Energy, L = 0.1mH (Note 8)		Eas	9.8	mJ

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

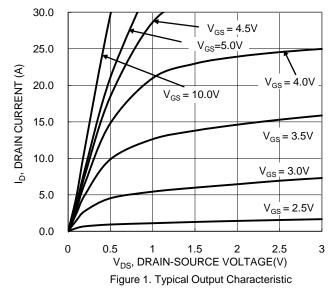
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		$P_{D}$	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	146	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)  Steady State		$R_{ heta JA}$	57	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	4.5	C/VV
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol Min Typ Max		Unit	Test Condition			
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	>	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	$\mu A$ $V_{DS} = 30V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	-	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Pages	-	13	18	mΩ	$V_{GS} = 10V, I_D = 7A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	21	30		$V_{GS} = 4.5V, I_{D} = 7A$	
Diode Forward Voltage	$V_{SD}$	-	0.7	1.2	<b>V</b>	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	-	500	-	рF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	-	72	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	57	-	pF		
Gate Resistance	$R_{g}$	-	1.9	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	-	4.6	-	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	9.8	-	nC	V <sub>DS</sub> = 15V. I <sub>D</sub> = 10A	
Gate-Source Charge	Q <sub>gs</sub>	-	1.6	-	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A	
Gate-Drain Charge	Q <sub>gd</sub>	-	2.0	-	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	3.9	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 6\Omega, I_D = 1A$	
Turn-On Rise Time	t <sub>R</sub>	-	4.2	-	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	16.6	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	5.8	-	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	5.6	-	ns	1 404 11/14 4004/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	2.6	-	nC	$I_F = 12A$ , di/dt = 100A/µs	

- Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  - 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J}$  = +25°C.
  - 9. Short duration pulse test used to minimize self-heating effect.
  - 10. Guaranteed by design. Not subject to product testing.





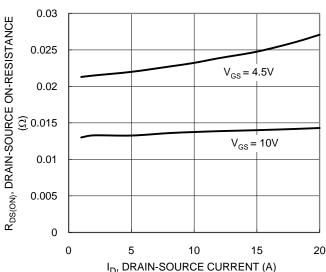


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

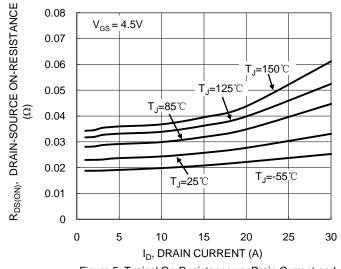


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

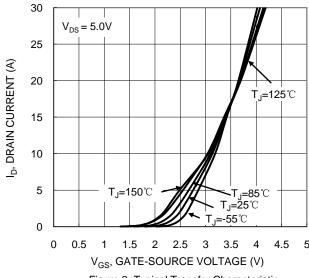


Figure 2. Typical Transfer Characteristic

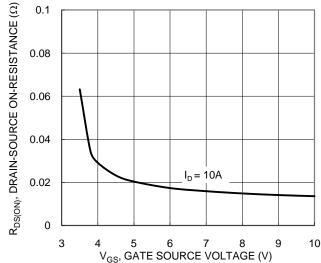


Figure 4. Typical On-Resistance vs. Drain Current and Gate Voltage

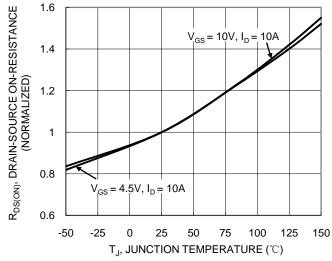
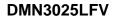


Figure 6. On-Resistance Variation with Temperature





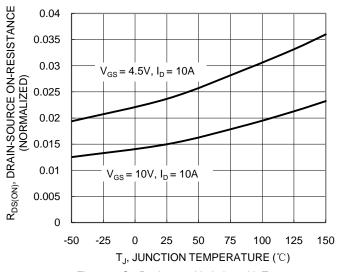
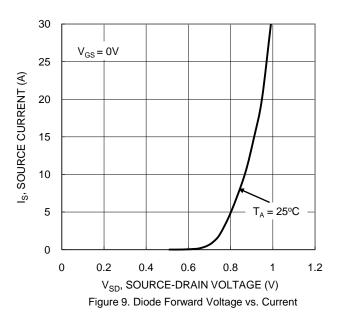
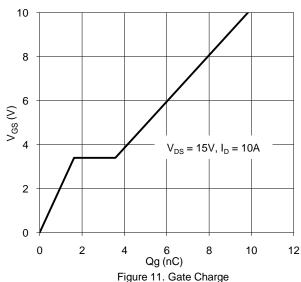


Figure 7. On-Resistance Variation with Temperature





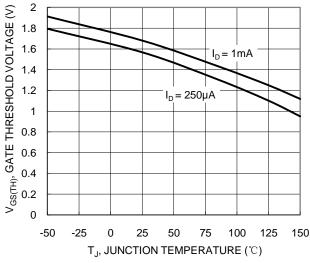
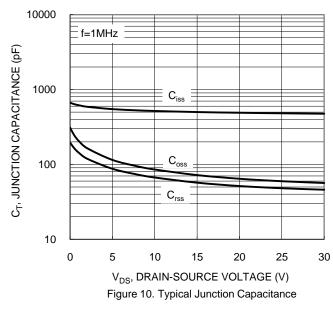
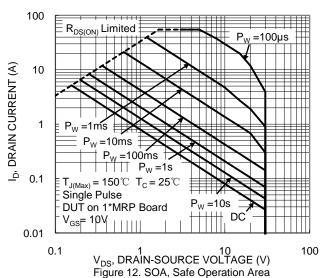


Figure 8. Gate Threshold Variation vs. Junction Temperature





December 2017

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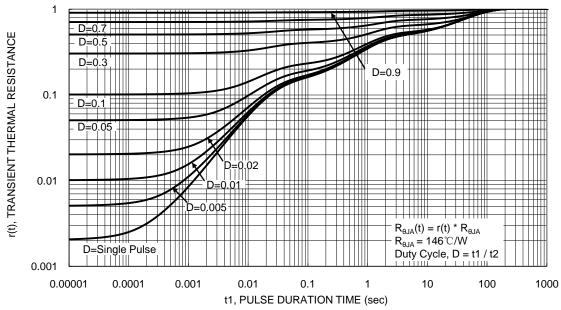


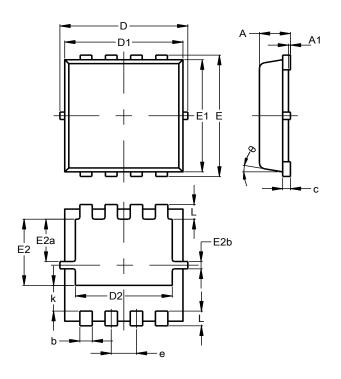
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)

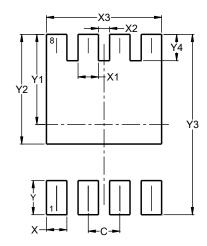


PowerDI3333-8 (Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E2a	0.95	1.35	1.15			
E2b	0.10	0.30	0.20			
е	0.65 BSC					
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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